**TOSHIBA 1SS361** 

#### TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

# 1 S S 3 6 1

#### ULTRA HIGH SPEED SWITCHING APPLICATION.

Small Package

 $V_{\rm F} = 0.9 V \, ({\rm Typ.})$ Low Forward Voltage

Fast Reverse Recovery Time :  $t_{rr} = 1.6ns$  (Typ.)

Small Total Capacitance  $: C_T = 0.9 pF (Typ.)$ 

### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Maximum (Peak) Reverse Voltage	$v_{ m RM}$	85	V	
Reverse Voltage	$ $ $v_{ m R}$	80	V	
Maximum (Peak) Forward Current	$I_{FM}$	300*	mA	
Average Forward Current	IO	100*	mA	
Surge Current (10ms)	$I_{FSM}$	2*	A	
Power Dissipation	P	100	mW	
Junction Temperature	$T_{j}$	125	°C	
Storage Temperature	$T_{ m stg}$	-55~125	°C	

 $1.6 \pm 0.2$  $0.8 \pm 0.1$ 0.5  $1.0 \pm 0.1$ ANODE 2. ANODE 3. CATHODE **JEDEC EIAJ** TOSHIBA 1-2S1B

Unit in mm

Weight: 2.4mg

\* Unit Rating. Total Rating=Unit Rating×1.5

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

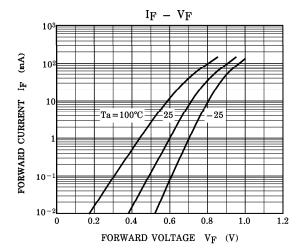
ELECTRICAL CHARACTERISTICS (TU = 25 C)								
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT		
Forward Voltage	$V_{F(1)}$	$I_{\mathbf{F}} = 1 \text{mA}$	_	0.60	_	v		
	$V_{F(2)}$	$I_{\mathbf{F}} = 10 \text{mA}$	_	0.72				
	$V_{F(3)}$	$I_{\mathbf{F}} = 100 \text{mA}$	_	0.90	1.20			
Reverse Currunt $ \frac{I_{R(1)}}{I_{R(2)}} $	I <sub>R (1)</sub>	$V_R=30V$	_	_	0.1	$\mu$ A		
	I <sub>R (2)</sub>	$V_R = 80V$	_	_	0.5			
Total Capacitance	$\mathrm{C}_{\mathbf{T}}$	$V_R = 0$ , $f = 1MHz$	_	0.9	3.0	рF		
Reverse Recovery Time	t <sub>rr</sub>	$I_{\mathbf{F}} = 10$ mA, Fig.1	_	1.6	4.0	ns		

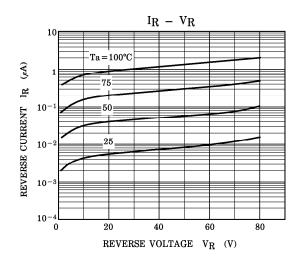
#### Marking

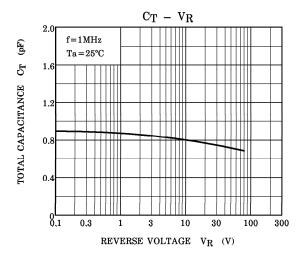


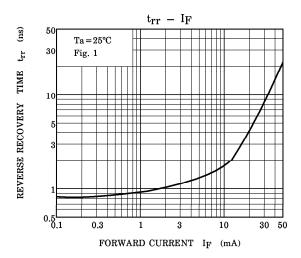
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